

Silicon Schottky Diodes

- For low-loss, fast-recovery, meter protection, bias isolation and clamping application
- Integrated diffused guard ring
- Low forward voltage



BAT64BAT64-02V
BAT64-02WBAT64-04
BAT64-04T
BAT64-04WBAT64-05
BAT64-05WBAT64-06
BAT64-06W31231111231111

ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Package	Configuration	L_S (nH)	Marking
BAT64	SOT23	single	1.8	63s
BAT64-02V*	SC79	single	0.6	t
BAT64-02W	SCD80	single	0.6	64
BAT64-04	SOT23	series	1.8	64s
BAT64-04T*	SC75	series	1.6	S1
BAT64-04W	SOT323	series	1.4	64s
BAT64-05	SOT23	common cathode	1.8	65s
BAT64-05W	SOT323	common cathode	1.4	65s
BAT64-06	SOT23	common anode	1.8	66s
BAT64-06W	SOT323	common anode	1.4	66s

* Preliminary data



Maximum Rating	s at $T_A =$	25°C, unless	otherwise	specified
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Parameter	Symbol	Value	Unit
Diode reverse voltage	V _R	40	V
Forward current	I _F	250	mA
Non-repetitive peak surge forward current	/ _{FSM}	800	
(<i>t</i> ≤ 10ms)			
Average forward current (50/60Hz, sinus)	I _{FAV}	120	
Total power dissipation	P _{tot}		mW
BAT64, <i>T</i> _S ≤ 86°C		250	
BAT64-02V, BAT64-02W, <i>T</i> _S ≤ 121°C		250	
BAT64-04, BAT64-06, <i>T</i> _S ≤ 61°C		250	
BAT64-04W, BAT64-06W, <i>T</i> _S ≤ 111°C		250	
BAT64-05, <i>T</i> _S ≤ 36°C		250	
BAT64-05W, <i>T</i> _S ≤ 104°C		250	
BAT64-04T, $T_{S} \le tbd$		250	
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-55 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}		K/W
BAT64		≤ 255	
BAT64-02V, BAT64-02W		≤ 115	
BAT64-04, BAT64-06,		≤ 355	
BAT64-04W, BAT64-06W		≤ 155	
BAT64-05		≤ 455	
BAT64-05W		≤ 185	
BAT64-04T		tbd	

¹For calculation of $R_{\rm thJA}$ please refer to Application Note Thermal Resistance



Parameter	Symbol		Unit		
		min.	typ.	max.	
DC Characteristics					
Breakdown voltage	V _(BR)	40	-	-	V
<i>I</i> _(BR) = 10 μA					
Reverse current	l _R				μA
$V_{\rm R} = 30 {\rm V}$		-	-	2	
$V_{\rm R} = 30 \text{ V}, \ T_{\rm A} = 85 \text{ °C}$		-	-	200	
Forward voltage	V _F				mV
$I_{\rm F} = 1 {\rm mA}$		270	320	350	
/ _F = 10 mA		310	385	430	
I _F = 30 mA		370	440	520	
/ _F = 100 mA		500	570	750	
AC Characteristics	-				
Diode capacitance	CT	-	4	6	pF
$V_{\rm R} = 1 {\rm V}, f = 1 {\rm MHz}$					
Reverse recovery time	<i>t</i> _{rr}	-	-	5	ns
$I_{\rm F}$ = 10 mA, $I_{\rm R}$ = 10 mA, measured $I_{\rm R}$ = 1 mA ,					
<i>R</i> _L = 100 Ω					

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified



Diode capacitance $C_{\rm T} = f (V_{\rm R})$

f = 1 MHz



Reverse current $I_{R} = f(V_{R})$

 T_A = Parameter



Forward current $I_{\rm F} = f (V_{\rm F})$

 T_A = Parameter



Forward current $I_{\rm F} = f (T_{\rm S})$ BAT64W





BAT64...

Forward current $I_{F} = f(T_{S})$ BAT64-02V, BAT64-02W



Forward current $I_F = f(T_S)$ BAT64-04, BAT64-06



Forward current $I_{F} = f (T_{S})$ BAT64-04W, BAT64-06W



Forward current $I_{F} = f(T_{S})$ BAT64-05





Forward current $I_{\rm F} = f(T_{\rm S})$

BAT64-05W



Permissible Puls Load $R_{thJS} = f(t_p)$ BAT64-02V, BAT64-02W



Permissible Pulse Load

 $I_{Fmax}/I_{FDC} = f(t_p)$ BAT64-02V, BAT64-02W



Permissible Puls Load $R_{thJS} = f(t_p)$ BAT64-04W, BAT64-06W





Permissible Pulse Load

 $I_{\text{Fmax}} / I_{\text{FDC}} = f(t_{\text{p}})$ BAT64-04W, BAT64-06W



Permissible Pulse Load

 $I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$ BAT64-05W



Permissible Puls Load $R_{thJS} = f(t_p)$ BAT64-05W

















Data Code marking for discrete packages with one digit (SCD80, SC79) CES-Code

Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	а	р	А	Р	а	р	А	Р	а	р	А	Р
02	b	q	В	Q	b	q	В	Q	b	q	В	Q
03	с	r	С	R	с	r	С	R	с	r	С	R
04	d	s	D	S	d	S	D	S	d	s	D	S
05	е	t	E	Т	е	t	E	Т	е	t	E	Т
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	v	G	V	g	v	G	V	g	v	G	V
08	h	х	н	Х	h	х	Н	Х	h	х	Н	Х
09	j	У	J	Y	j	У	J	Y	j	У	J	Y
10	k	z	К	Z	k	z	К	Z	k	z	К	Z
11	I	2	L	4	I	2	L	4	I	2	L	4
12	n	3	N	5	n	3	N	5	n	3	Ν	5











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